

Code: EE2T4

I B.Tech - II Semester – Regular Examinations – April 2016

**BASIC ELECTRONIC DEVICES AND CIRCUITS
(ELECTRICAL & ELECTRONICS ENGINEERING)**

Duration: 3 hours

Max. Marks: 70

PART – A

Answer *all* the questions. All questions carry equal marks

11x 2 = 22 M

1. a) Differentiate between static and dynamic resistances.
- b) Explain diode as a switch.
- c) Give any four advantages of FET over BJT.
- d) Differentiate between enhancement mode and depletion mode operations of MOSFET.
- e) Define stability factors S , S^I and S^{II} .
- f) Explain need for biasing.
- g) Draw the transistor hybrid model circuit.
- h) Write the Barkhausen criterion.
- i) What are the advantages of negative feedback?
- j) Write the applications of RC oscillators.
- k) Why CC amplifier called as Emitter follower?

PART – B

Answer any **THREE** questions. All questions carry equal marks. 3 x 16 = 48 M

2. a) Draw I-V characteristics of a silicon junction diode and explain. 8 M
- b) Derive the expression for ripple factor of full wave rectifier with capacitor filter. 8 M
3. a) A BJT has $\alpha=0.99$, $I_B=25\mu\text{A}$ and $I_{CBO}=200\text{nA}$. Find
- i) the dc collector current
 - ii) the dc emitter current and
 - iii) the percentage error in emitter current when leakage current is neglected. 8 M
- b) Explain the operation of JFET with neat drain characteristics. 8 M
4. a) Explain the different bias compensation techniques to reduce the drift of the operating point. 8 M
- b) Explain the self bias circuit and derive the operating point. 8 M
5. a) Analyze a Single stage transistor amplifier using h-parameters. 8 M

b) Derive the high frequency parameters transconductance and input conductance of a transistor in terms of low frequency parameters. 8 M

6. a) Draw and explain the RC phase shift oscillator. Also derive the condition for oscillations. 8 M

b) Draw and explain feedback topologies. Give the effect of negative feedback on input and output resistances of these topologies. 8 M